



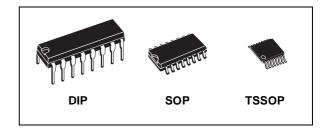
## **QUAD BILATERAL SWITCH**

- HIGH SPEED:
  - $t_{PD}$  = 13ns (TYP.) at  $V_{CC}$  = 6V
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $V_{cc} = 5V$
- LOW "ON" RESISTANCE: 120Ω TYP.  $(V_{CC} - V_{EE} = 2V)$  50Ω TYP.  $(V_{CC} - V_{EE} = 4.5V)$ 35Ω TYP.  $(V_{CC} - V_{EE} = 9V)$
- WIDE ANALOG INPUT VOLTAGE RANGE ± 6v
- LOW CROSSTALK BETWEEN SWITCHES
- **■** FAST SWITCHING
- SINE WAVE DISTORTION: 0.020 at V<sub>CC</sub> - V<sub>EE</sub> = 9V
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28 % V<sub>CC</sub> (MIN.)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 4316

#### **DESCRIPTION**

The M74HC4316 is an high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate C<sup>2</sup>MOS technology.

This device has four independent analogue switches. Each switch has two input/output terminals (nI/O, nO/I) and an active high select input (nC).



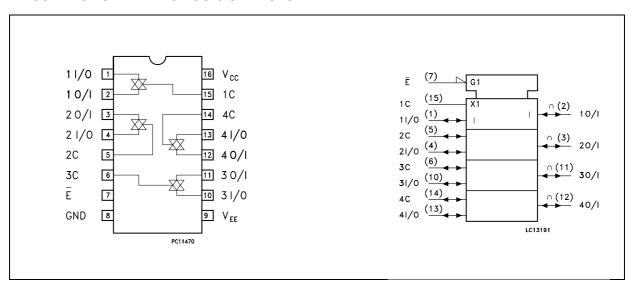
#### **ORDER CODES**

PACKAGE	TUBE	T & R
DIP	M74HC4316B1R	
SOP	M74HC4316M1R	M74HC4316RM13TR
TSSOP		M74HC4316TTR

When the enable input is high, all four analog switches are off. The supply voltage for the digital signals applied to  $V_{CC}$  and GND must be whitin the range 0 to 6 V. The voltage swing on the analogue Inputs/Outputs can be between  $V_{CC}$  (positive limit) and  $V_{EE}$  (negative limit). The voltage between  $V_{CC}$  and  $V_{EE}$  must not exceed 12V.

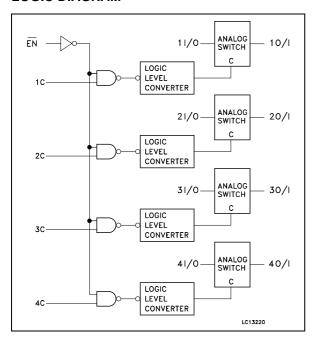
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/11

## **LOGIC DIAGRAM**



## **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	1 to 4 I/O	Independent Inputs/Outputs
2, 3, 11, 12	1 to 4 O/I	Independent Outputs/ Inputs
7	Ē	Enable Inputs (Active LOW)
15, 5, 6, 14	1C to 4C	Enable Inputs (Active High)
9	$V_{EE}$	Negative Supply Voltage
8	GND	Ground (0V)
16	V <sub>CC</sub>	Positive Supply Voltage

## **TRUTH TABLE**

Ē	С	SWITCH FUNCTION
L	Н	ON
L	L	OFF
Н	Х	OFF

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>CC</sub> - V <sub>EE</sub>	Supply Voltage	-0.5 to +13	V
V <sub>I</sub>	Control Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>I/O</sub>	Switch Input/Output Voltage	$V_{EE}$ -0.5 to $V_{CC}$ + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Io	DC Output Source Sink Current Per Output Pin	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
$P_{D}$	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied (\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	Supply Voltage		2 to 12	V
V <sub>EE</sub>	Supply Voltage		-6 to 0	V
V <sub>CC</sub> - V <sub>EE</sub>	Supply Voltage		2 to 12	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V	
V <sub>I/O</sub>	Switch I/O Voltage		0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	
t <sub>r</sub> , t <sub>f</sub>		V <sub>CC</sub> = 4.5V	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	

## **DC SPECIFICATIONS**

		Test Condition			Value							
Symbol	Parameter	V <sub>CC</sub>	V <sub>EE</sub>		T	T <sub>A</sub> = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
$V_{IHC}$	High Level	2.0			1.5			1.5		1.5		
	Control Input	4.5			3.15			3.15		3.15		V
	Voltage	6.0			4.2			4.2		4.2		
$V_{ILC}$	Low Level Control	2.0					0.5		0.5		0.5	
	Input Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
R <sub>ON</sub>	ON Resistance	4.5	GND	1 1110		70	170		200			
		4.5	-4.5	$V_{I/O} = V_{CC}$ to $V_{EE}$		50	85		105			
		6.0	-6.0	$I_{I/O} = 0.1 mA$		30	70		85			
	2.0 GND	V - V		120	180		215			Ω		
		4.5	GND	$V_{I} = V_{IHC}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$		50	80		100			
		4.5	-4.5	$I_{1/O} = 0.1 \text{mA}$		35	60		75			
		6.0	-6.0	1//0 = 0.1111/1		20	40		60			
$\Delta R_{ON}$	Difference of ON	4.5	GND	$V_{IN} = V_{IHC}$ or $V_{ILC}$		10	15		20			
	Resistance	4.5	-4.5	$V_{I/O} = V_{CC}$ to $V_{EE}$		5	10		15			Ω
	between switches	6.0	-6.0	$I_{I/O} = 0.1 mA$		5	10		15			
I <sub>OFF</sub>	Input/Output	6.0	GND	$V_{OS} = V_{CC}$ or GND			±0.06		± 0.6		± 2	
	Leakage Current (SWITCH OFF)	6.0	-6.0	$V_{IS} = V_{CC}$ or GND $V_{IN} = V_{IHC}$ or $V_{ILC}$			± 0.1		± 1		± 2	μΑ
I <sub>IZ</sub>	Switch Input	6.0	GND	., ., .,			±0.06		± 0.6		± 2	μА
12	Leakage Current (SWITCH ON, OUTPUT OPEN)	6.0		$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IHC}$ or $V_{ILC}$			± 0.1		± 1		± 2	•
I <sub>IN</sub>	Control Input Current	6.0	V	I = V <sub>CC</sub> or GND		10 <sup>-5</sup>	± 0.1		± 1		± 1	μΑ

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ns}$ )

			Test	Condition				Value				
Symbol	Parameter	v <sub>cc</sub>	VEE		T <sub>A</sub> = 25°C			-40 to	85°C	-55 to 125°C		Unit
		(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
$\Phi_{I/O}$	Phase Difference	2.0	GND			12	30		40			
	Between Input	4.5	GND			3	6		8			
	and Output	6.0	GND			3	5		7			ns
	4.5	-4.5			2	4		5				
		6.0	-6.0			2	4		5			
t <sub>PZL</sub>	t <sub>DZL</sub> Time	2.0	GND			56	115		145			
t <sub>PZH</sub>		4.5	GND			14	23		29			
	(Ē, C - OUT)	6.0	GND	$R_L = 1K\Omega$		12	20		25			ns
		4.5	-4.5			13	21		26			
		6.0	-6.0			11	18		23			
t <sub>PLZ</sub>	Output Disable	2.0	GND			112	205		255			
t <sub>PHZ</sub>	Time	4.5	GND			28	41		51			
	(E, C - OUT)	6.0	GND	$R_L = 1K\Omega$		24	35		43			ns
		4.5	-4.5			24	34		43			
		6.0	-6.0			21	29		36			
f <sub>MAX</sub>	Maximum Control	2.0	GND	$R_L = 1K\Omega$		2						
	Input Frequency	4.5	GND	$C_{L} = 15  pF$		9						MHz
		6.0	GND	$V_{OUT} = 1/2 V_{CC}$		11						

## **CAPACITIVE CHARACTERISTICS**

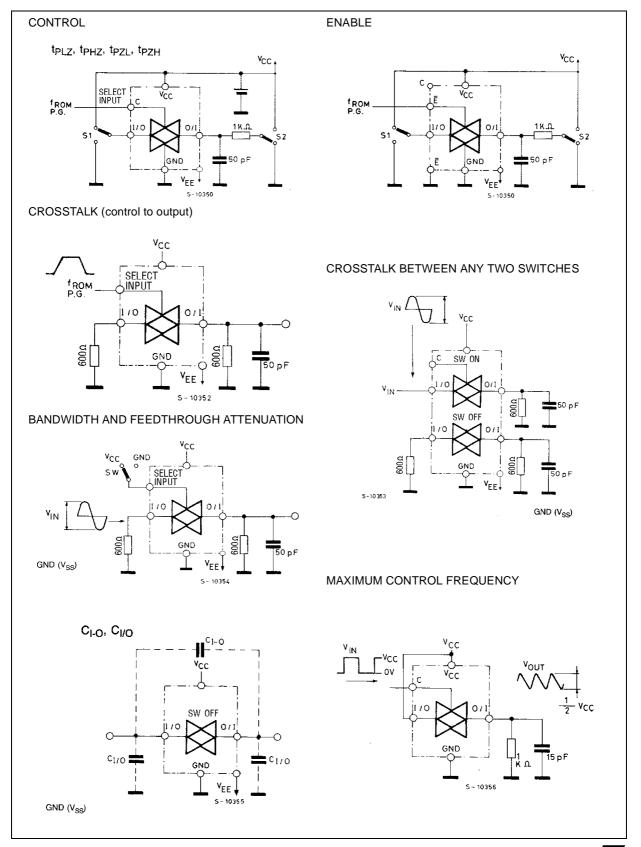
		1	Test Condition		Value						
Symbol	Parameter	V <sub>CC</sub>		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)	·	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance				5	10		10		10	pF
C <sub>I/O</sub>	Switch Terminal Capacitance	4.5	-4.5		5						pF
C <sub>IOS</sub>	Feed Through Capacitance	4.5	-4.5		1						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0	GND		16						pF

<sup>1)</sup> C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> + I<sub>CC</sub>

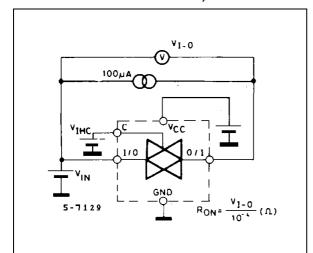
# ANALOG SWITCH CHARACTERISTICS (GND = $0V;T_A = 25$ °C)

Symbol	Parameter				Test Condition	Value	Unit
		V <sub>CC</sub> (V)	V <sub>EE</sub> (V)	V <sub>IN</sub> (V <sub>p-p</sub> )		Тур.	
	Sine Wave	2.25	2.25	4		0.025	
	Distortion (THD)	4.5	4.5	8	$f_{IN}$ = 1 KHz $R_L$ = 10 K $\Omega$ , $C_L$ = 50 pF	0.020	%
		6.0	6.0	11		0.018	
f <sub>MAX</sub>	Frequency	2.25	2.25		Adjust f <sub>IN</sub> voltage to obtain 0 dBm at V <sub>OS</sub> .	28	
	Response	4.5	4.5	1	Increase f <sub>IN</sub> Frequency until dB meter reads -3dB		MHz
	(Switch ON)	6.0	6.0		$R_L = 50\Omega$ , $C_L = 10$ pF, $f_{IN} = 1$ MHz sine wave	43	
	Feed through	2.25	2.25		V <sub>IN</sub> is centered at V <sub>CC</sub> /2. Adjust input for 0 dBm	-50	
	Attenuation	4.5	4.5		$R_L = 600\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ MHz sine wave	-50	dB
	(Switch OFF)	6.0	6.0			-50	
	Crosstalk (Control	2.25	2.25				
	Input to Signal	4.5	4.5	$R_L = 6$	$00\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ MHz square wave $(t_r = t_f = 6$ ns)	5	mV
	Output)	6.0	6.0				
	Crosstalk	2.25	2.25		Adjust V <sub>IN</sub> to Obtain 0 dBm at input	-50	
	(Between Any	4.5	4.5		$R_L = 600\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ MHz sine wave	-50	dB
	Switches)	6.0	6.0			-50	

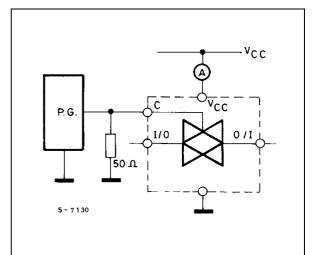
## **SWITCHING CARACTERISTICS TEST CIRCUIT**



# CHANNEL RESISTANCE (R<sub>ON)</sub>

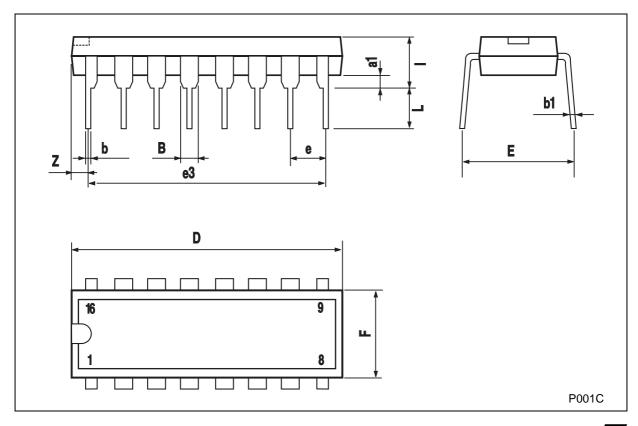


I<sub>CC</sub> (Opr.)



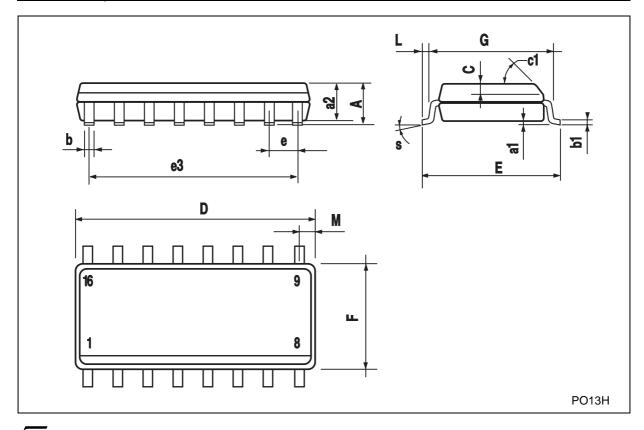
# Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



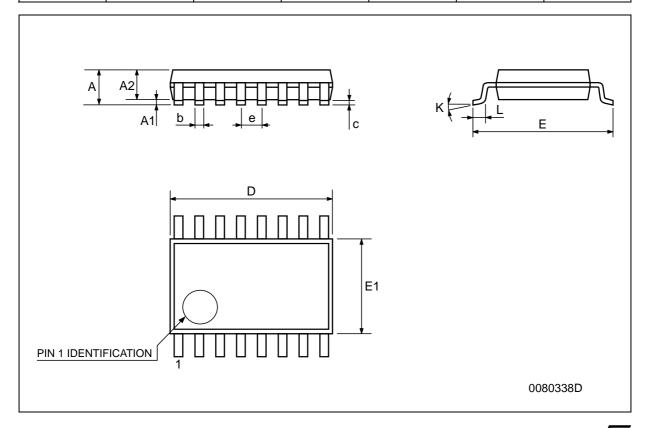
## **SO-16 MECHANICAL DATA**

DIM		mm.			inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
Α			1.75			0.068			
a1	0.1		0.2	0.003		0.007			
a2			1.65			0.064			
b	0.35		0.46	0.013		0.018			
b1	0.19		0.25	0.007		0.010			
С		0.5			0.019				
c1			45°	(typ.)	•				
D	9.8		10	0.385		0.393			
E	5.8		6.2	0.228		0.244			
е		1.27			0.050				
еЗ		8.89			0.350				
F	3.8		4.0	0.149		0.157			
G	4.6		5.3	0.181		0.208			
L	0.5		1.27	0.019		0.050			
М			0.62			0.024			
S			8° (	max.)	·				



## **TSSOP16 MECHANICAL DATA**

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco Singapore - Spain - Sweden - Switzerland - United Kingdom © http://www.st.com

